

SMB/DO-214AA

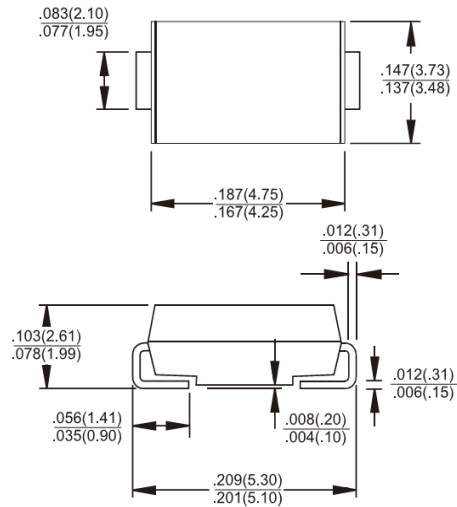
**RoHS
COMPLIANCE**

Features

- ✧ Glass passivated junction chip.
- ✧ For surface mounted application
- ✧ Low forward voltage drop
- ✧ Low profile package
- ✧ Built-in stain relief, ideal for automatic placement
- ✧ Fast switching for high efficiency
- ✧ High temperature soldering:
260°C/10 seconds at terminals
- ✧ Plastic material used carries Underwriters
Laboratory Classification 94V-0
- ✧ Green compound with suffix "G" on packing
code & prefix "G" on datecode

Mechanical Data

- ✧ Case: Molded plastic
- ✧ Terminal: Pure tin plated, lead free
- ✧ Polarity: Indicated by cathode band
- ✧ Packing: 12mm tape per EIA STD RS-481
- ✧ Weight: 0.093 grams


Dimensions in inches and (millimeters)
Marking Diagram


- HS3XB = Specific Device Code
 G = Green Compound
 Y = Year
 M = Work Month

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	HS 3AB	HS 3BB	HS 3DB	HS 3FB	HS 3GB	HS 3JB	HS 3KB	HS 3MB	Unit	
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V	
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V	
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V	
Maximum Average Forward Rectified Current	$I_{F(AV)}$	3								A	
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	100								A	
Maximum Instantaneous Forward Voltage (Note 1) @ 3 A	V_F	1.0			1.3		1.7			V	
Maximum Reverse Current @ Rated VR $T_A=25\text{ }^\circ\text{C}$ $T_A=125\text{ }^\circ\text{C}$	I_R	10 250								μA	
Maximum Reverse Recovery Time (Note 2)	T_{rr}	50					75				nS
Typical Junction Capacitance (Note 3)	C_j	80					50				pF
Typical Thermal Resistance	$R_{\theta JA}$	60								$^\circ\text{C/W}$	
Operating Temperature Range	T_J	- 55 to + 150								$^\circ\text{C}$	
Storage Temperature Range	T_{STG}	- 55 to + 150								$^\circ\text{C}$	

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

 Note 2: Reverse Recovery Test Conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES (HS3AB THRU HS3MB)

FIG.1 FORWARD CURRENT DERATING CURVE

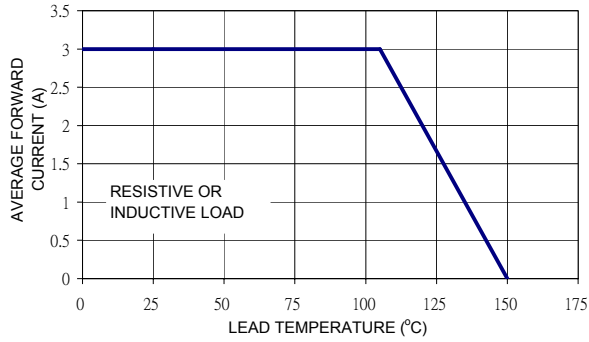


FIG. 2 TYPICAL REVERSE CHARACTERISTICS

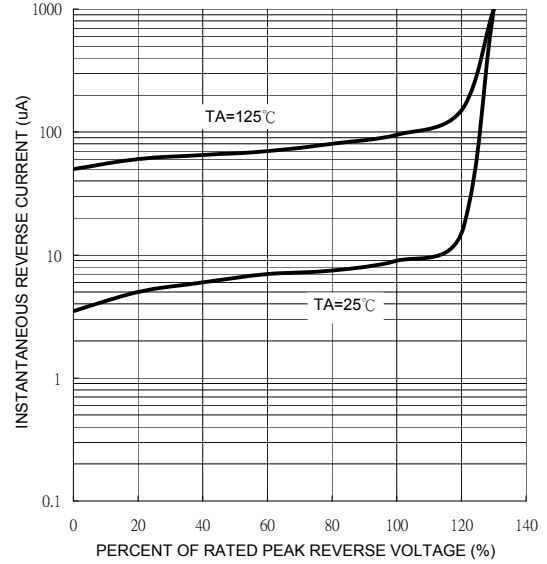


FIG. 3 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

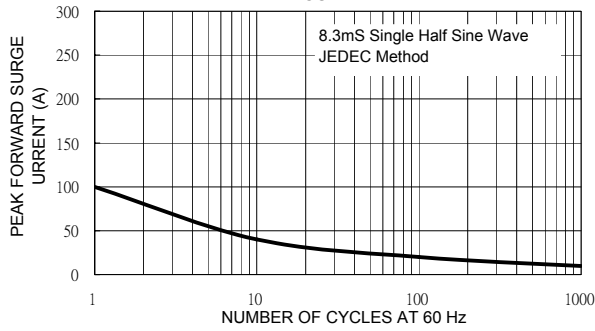


FIG. 5 TYPICAL FORWARD CHARACTERISTICS

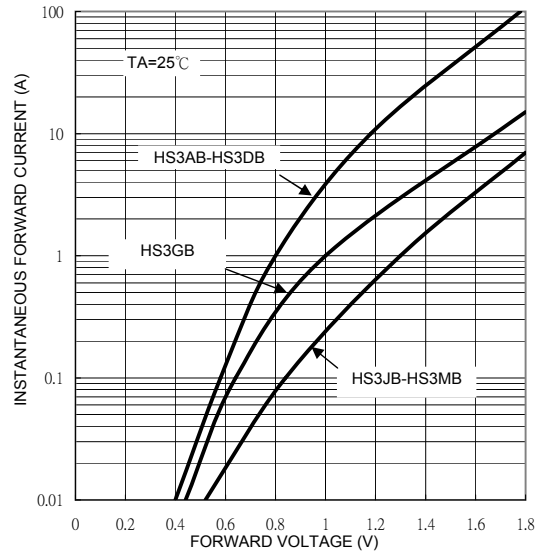


FIG. 4 TYPICAL JUNCTION CAPACITANCE

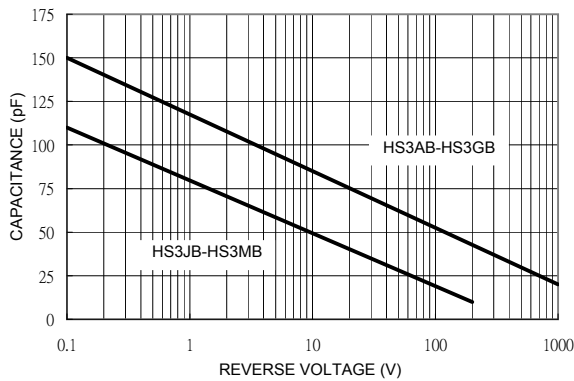


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

